Schottky barrier diode
RB420D

●Applications

Low power rectification

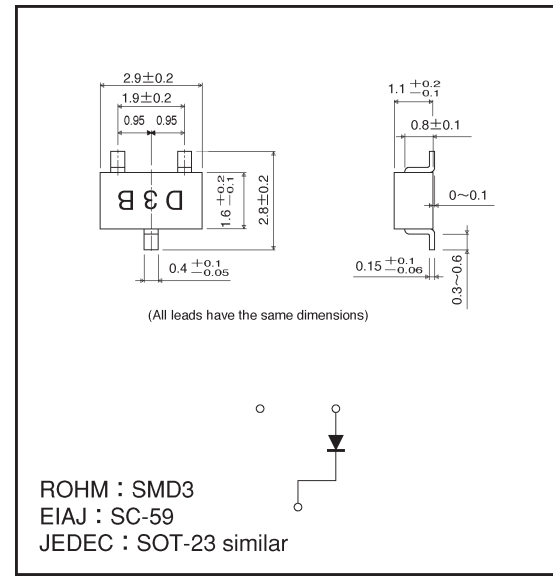
●Features

1) Dual element common cathode configuration in compact SMD3 package.
2) High reliability.
3) Low reverse current and low forward voltage.

●Construction

Silicon epitaxial planar

●External dimensions (Units: mm)



●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	40	V
DC reverse voltage	V_R	40	V
Mean rectifying current	I_O	0.1	A
Peak forward surge current*	I_{FSM}	1	A
Junction temperature	T_j	125	℃
Storage temperature	T_{stg}	−40～+125	℃

* 60 Hz for 1 ∽

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	—	0.36	0.45	V	I_F=10mA
Reverse current	I_R	—	0.05	1	μA	V_R=10V
Capacitance between terminals	C_T	—	6.0	—	pF	V_R=10V, f=1MHz

* ESD sensitive product handling required.

●Electrical characteristic curves (Ta = 25°C unless specified otherwise)

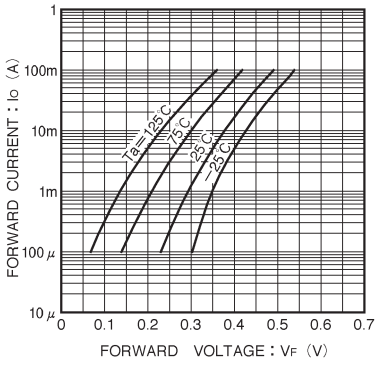


Fig. 1 Forward characteristics

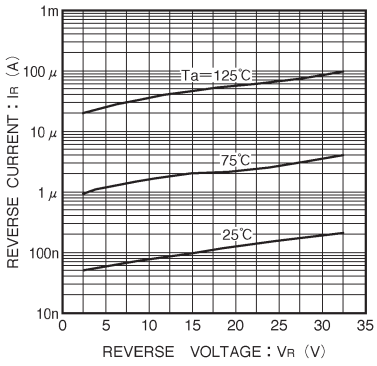


Fig. 2 Reverse characteristics

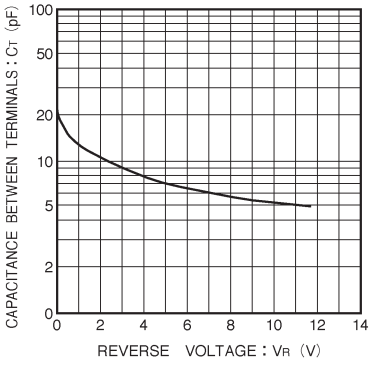


Fig. 3 Capacitance between terminals characteristics

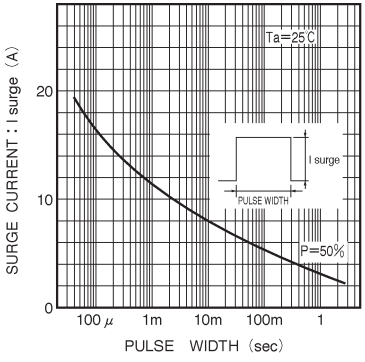


Fig. 4 Surge current characteristics

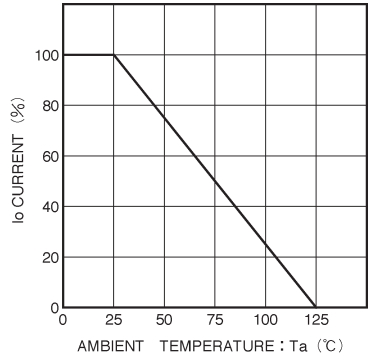


Fig. 5 Derating curve
(mounting on glass epoxy PCBs)